

General Description:

The LWT1H207H8 uses advanced SGT technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is TO-220AB, which accords with the ROHS standard and Halogen Free standard.

Free standard.

Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- Battery switching application
- Hard switched and high frequency circuits
- Power Management

100% DVDS Tested

100% Avalanche Tested



Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
T1H207/LW H8/D.C.	LWT1H207H8	TO-220AB	Tube	50 Pcs

Absolute Maximum Ratings:

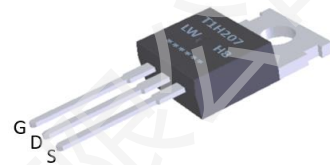
Symbol	Parameter	Value	Units
V_{DSS}	Drain-to-Source Voltage	120	V
I_D	Continuous Drain Current	$T_C=25^\circ C$	125
	Continuous Drain Current	$T_C=100^\circ C$	79
I_{DM}^{a1}	Pulsed Drain Current	500	A
E_{AS}^{a2}	Single pulse avalanche energy	324	mJ
V_{GS}	Gate-to-Source Voltage	± 20	V
P_D	Power Dissipation	227	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	150, -55 to 150	$^\circ C$
T_L	Maximum Temperature for Soldering	260	$^\circ C$

Thermal Characteristics:

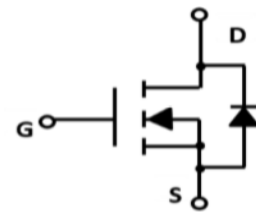
Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.55	$^\circ C/W$
$R_{\theta JA}^{a3}$	Thermal Resistance, Junction-to-Ambient	60	$^\circ C/W$

V_{DSS}	120	V
I_D	125	A
P_D	227	W
$R_{DS(ON) \text{ TYPE}}$	6.0	$m\Omega$

Marking and Pin Assignment



Inner Equivalent Principium Chart



Electrical Characteristic ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	120	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=120V, V_{GS}=0V$	--	--	1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+20V, V_{DS}=0V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-20V, V_{DS}=0V$	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	3.0	3.5	V
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=20A$	--	6.0	7.5	$m\Omega$

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0V$	--	4021	--	pF
C_{oss}	Output Capacitance	$V_{DS}=60V$	--	422	--	
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	--	7.8	--	
R_G	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	--	1.0	--	Ω

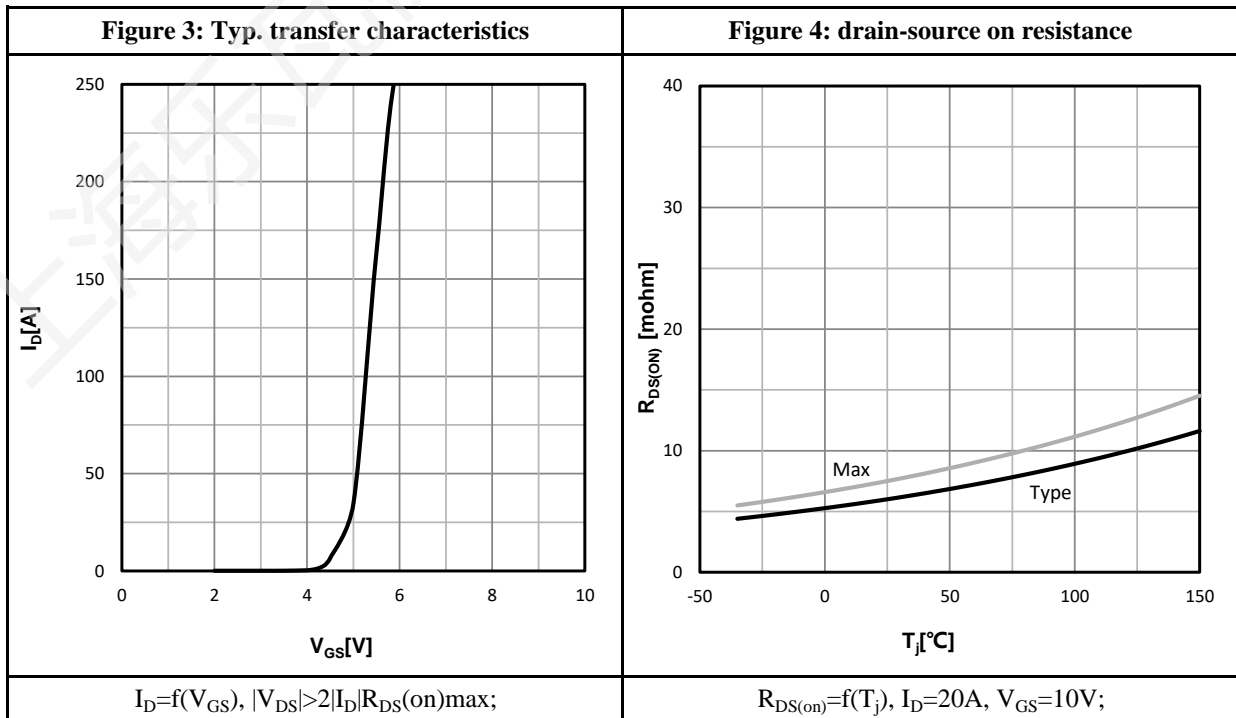
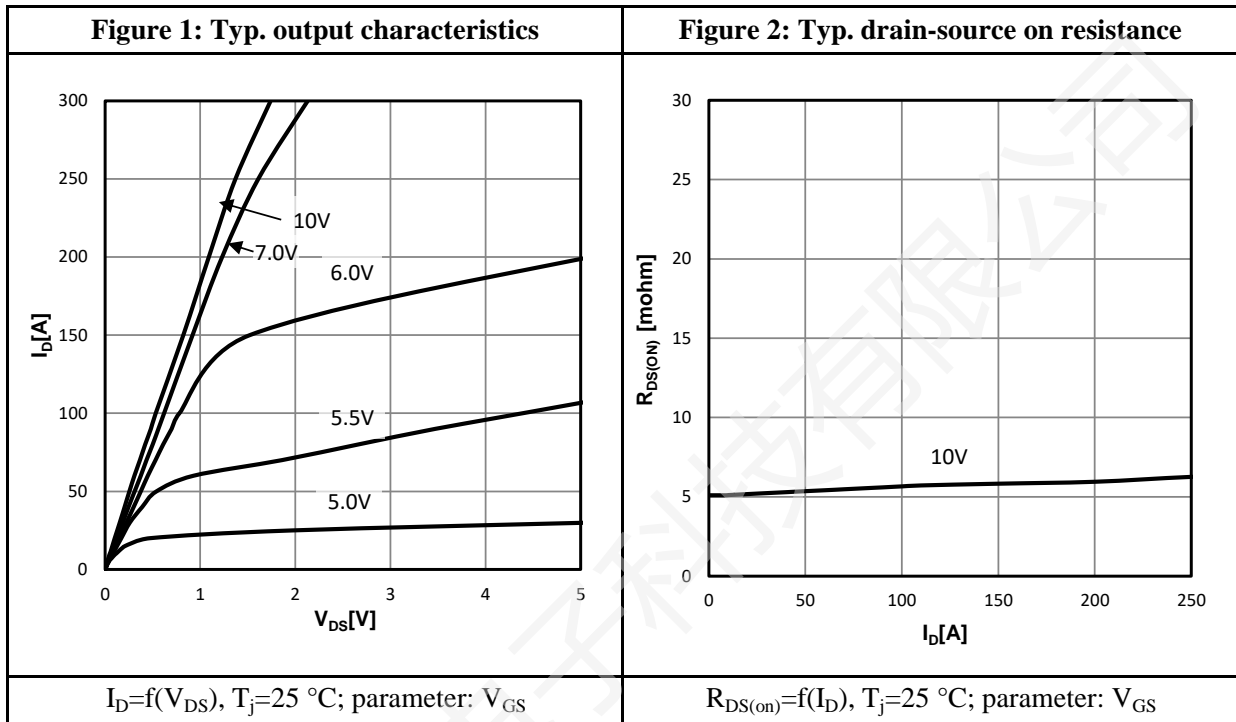
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=20A$ $V_{DS}=60V$ $V_{GS}=10V$ $R_G=5.0\Omega$	--	20	--	ns
t_r	Rise Time		--	65	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	32	--	
t_f	Fall Time		--	49	--	
Q_g	Total Gate Charge	$V_{GS}=10V$	--	60	--	nC
Q_{gs}	Gate to Source Charge	$V_{DS}=60V$	--	19	--	
Q_{gd}	Gate to Drain Charge	$I_D=20A$	--	14	--	

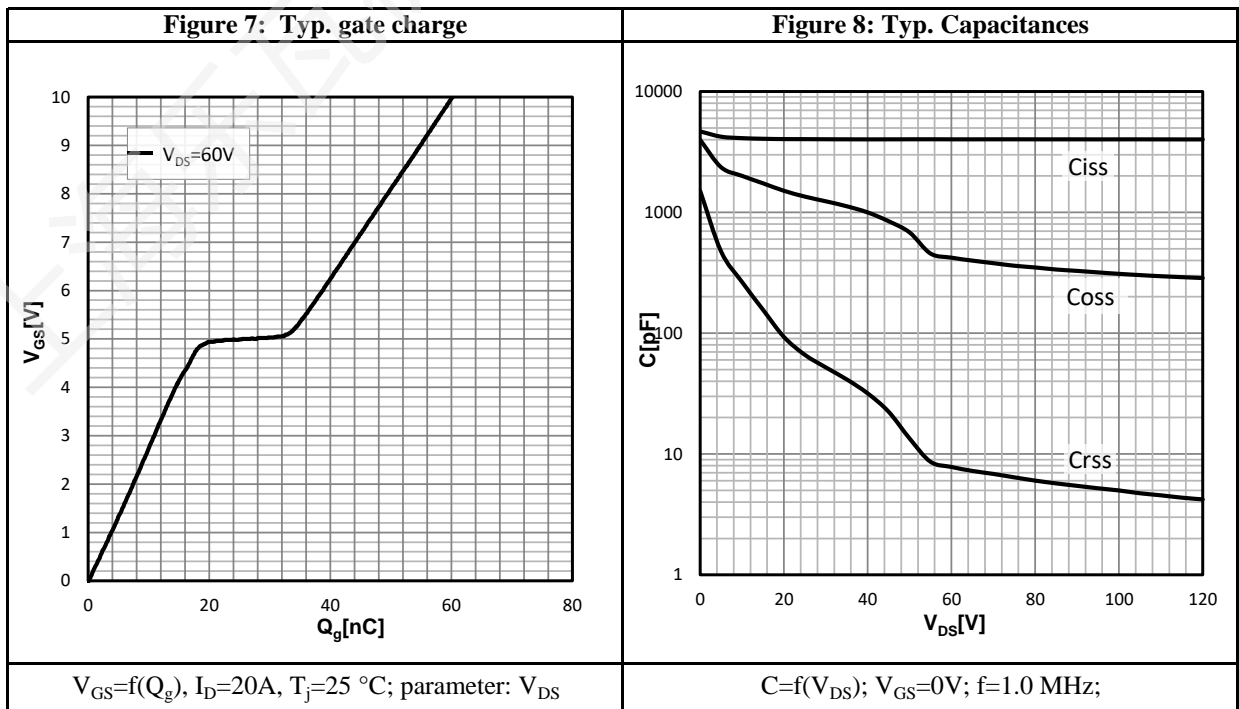
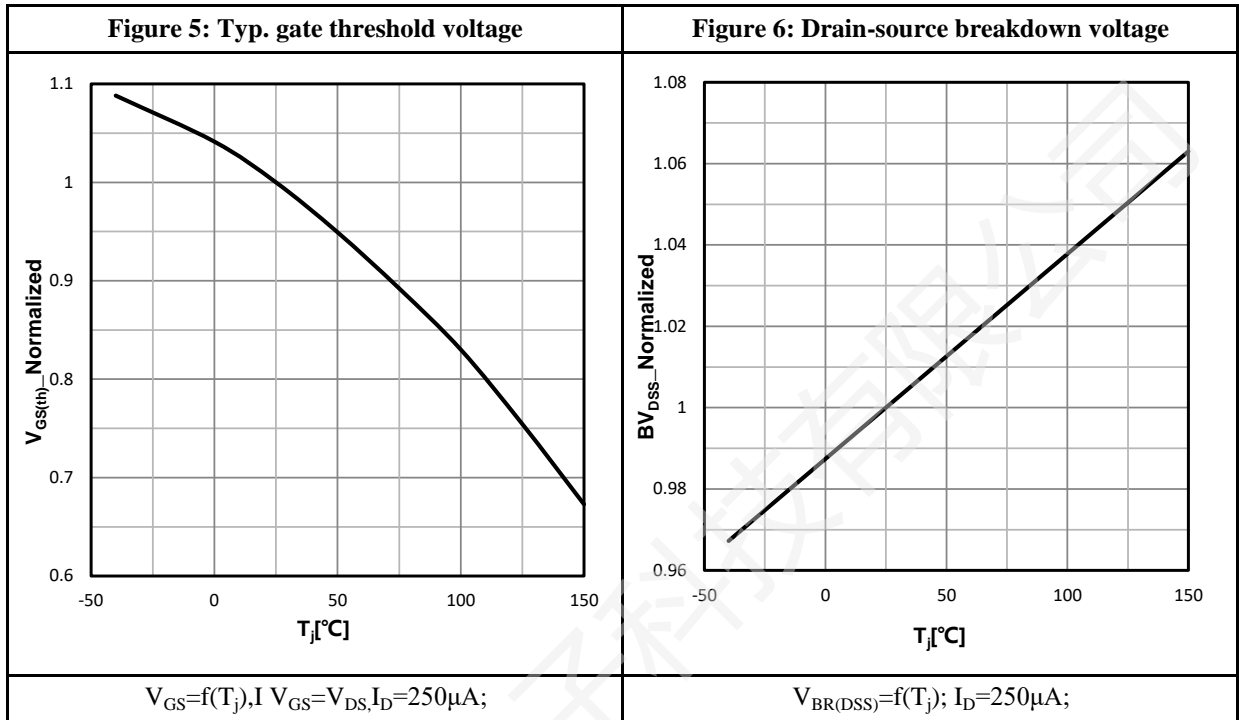
Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_C=25\text{ }^\circ\text{C}$	--	--	125	A
V_{SD}	Diode Forward Voltage	$I_S=20A, V_{GS}=0V$	--	--	1.2	V

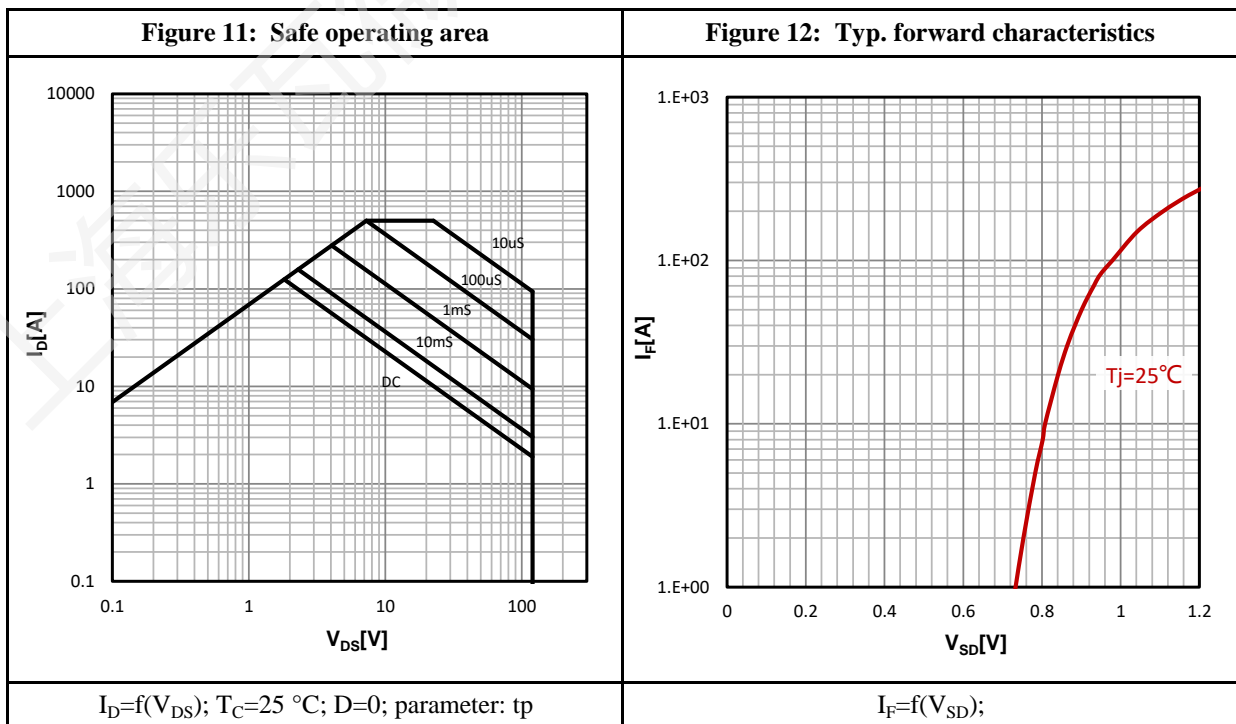
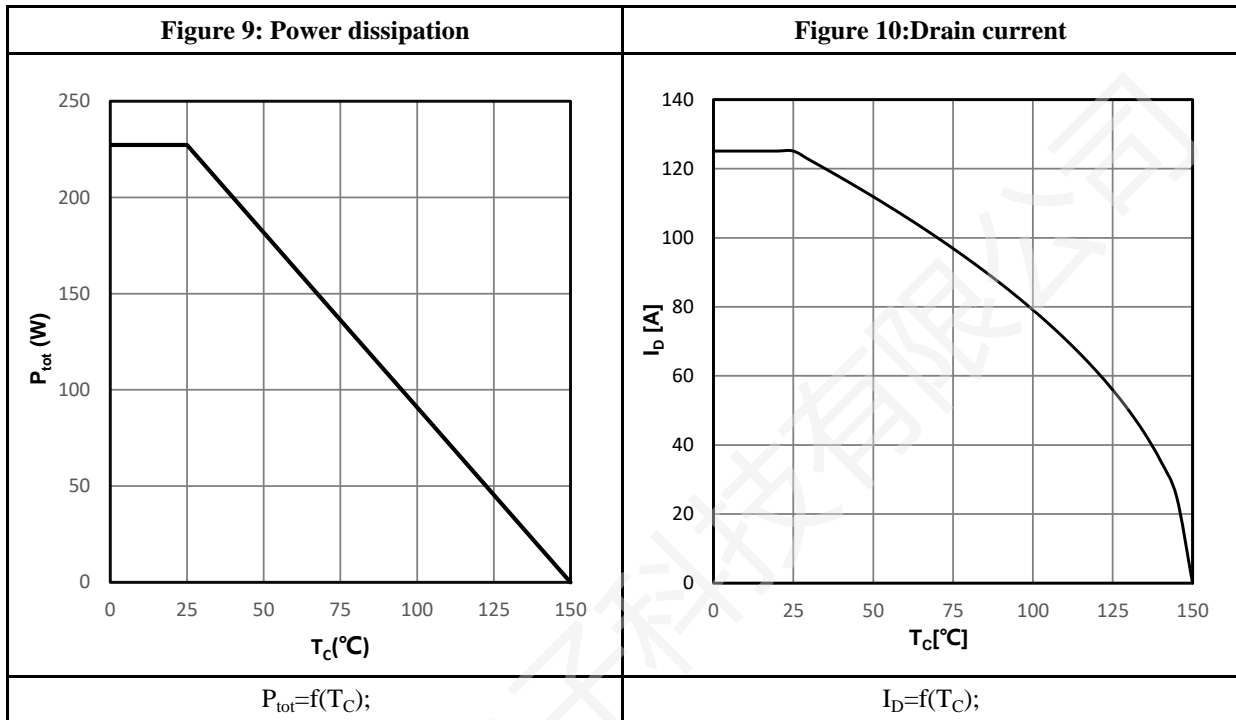
a1: Repetitive rating; pulse width limited by maximum junction temperature

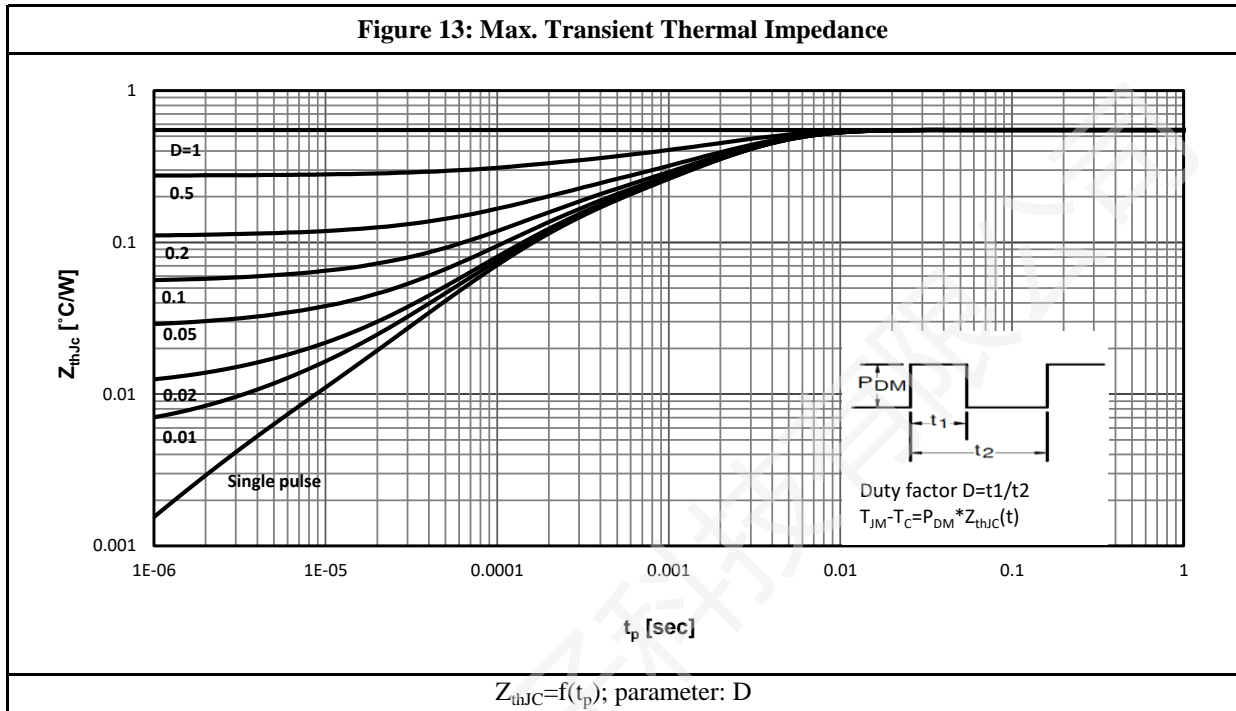
a2: $V_{DD}=60V, L=0.5mH, R_G=25\Omega$, Starting $T_J=25\text{ }^\circ\text{C}$

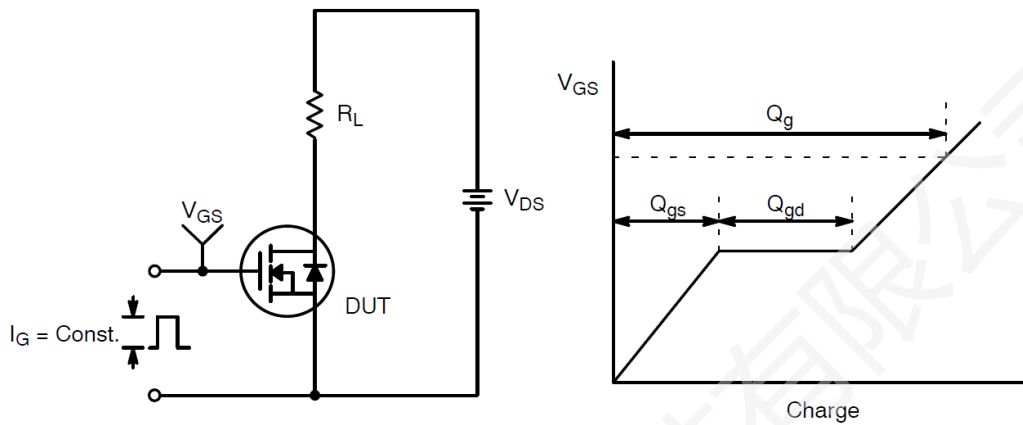
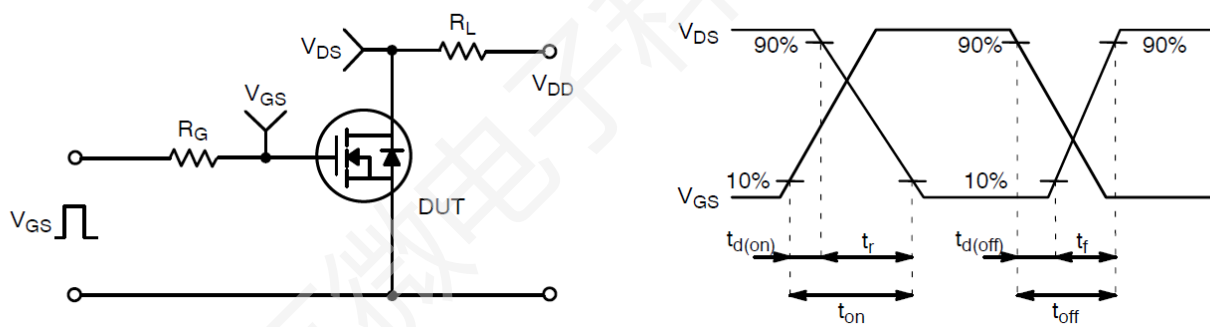
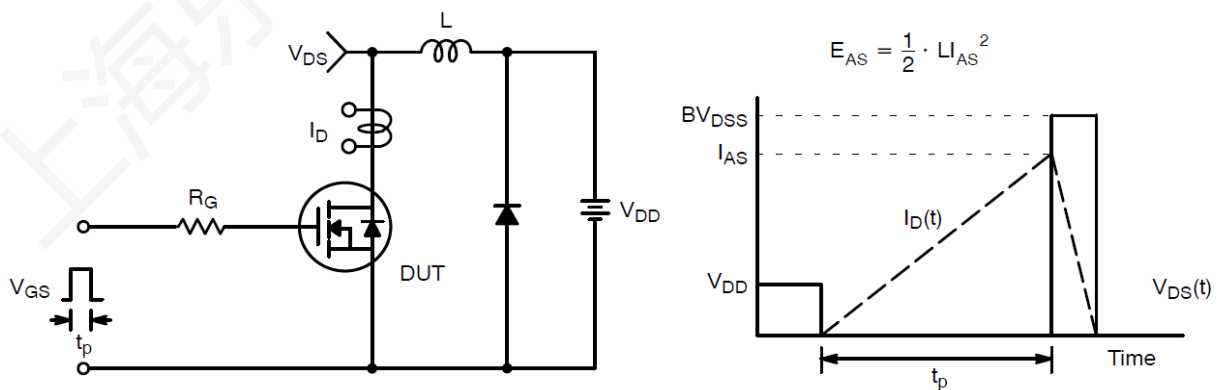
a3: Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection.

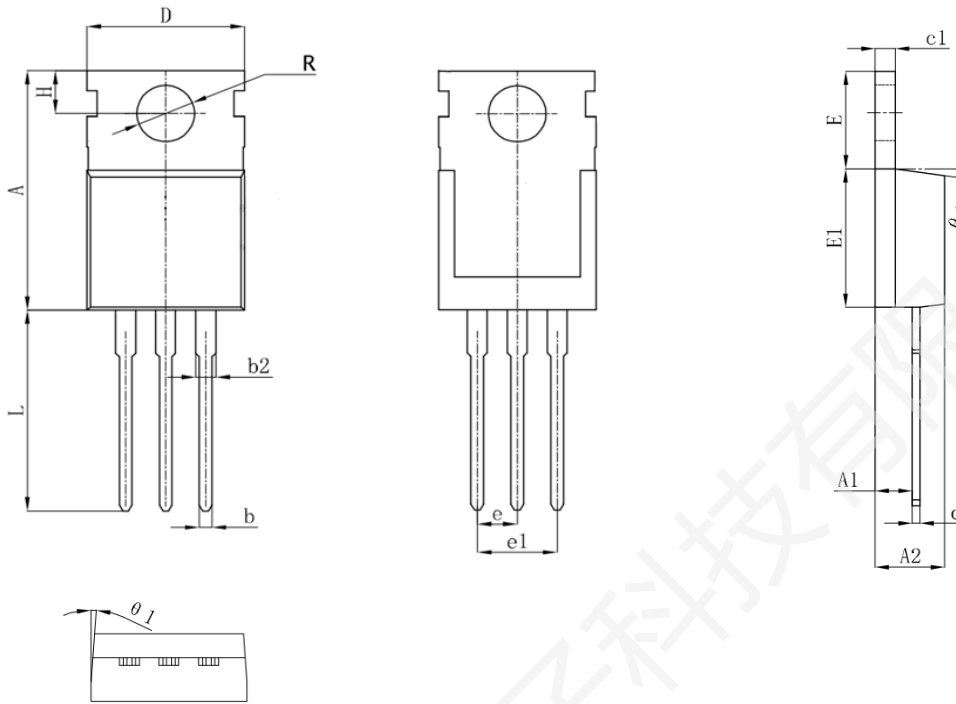
Characteristics Curve:








Test Circuit & Waveform:

Figure 14: Gate Charge Test Circuit & Waveform

Figure 15: Resistive Switching Test Circuit & Waveforms

Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:


SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	15.3	15.55	15.8
A1	2.3	2.4	2.5
A2	4.4	4.5	4.7
b	0.7	0.8	0.9
b2	1.18	1.31	1.44
c	0.44	0.5	0.56
c1	1.28	1.3	1.33
D	9.8	10	12.2
E	6.4	6.5	6.6
E1	8.9	9.05	9.2
e	2.42	2.54	2.66
e1	4.84	5.08	5.32
H	2.73	2.8	2.87
H1	2.4	2.5	2.6
L	13.02	13.42	13.82
R	3.5	3.6	3.63
θ1	2°	2.5°	3°
θ2	6.5°	7°	7.5°

Revision History:

Revison	Date	Descriptions
Rev 1.0	Dec.2022	Initial Version

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